

Large-Signal Transfer Function of Bipolar Differential Amplifier

■ $V_{OD} = V_{O1} - V_{O2}$

$$V_{O1} = V_{CC} - I_{C1} R_C \quad V_{O2} = V_{CC} - I_{C2} R_C$$

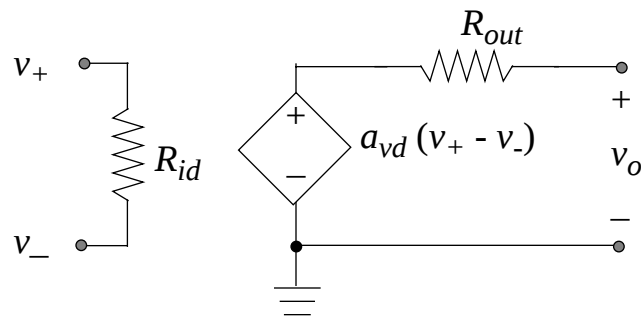
$$V_{OD} = (I_{C2} - I_{C1}) R_C = \alpha_F I_{BIAS} R_C \left(\frac{1}{1 + e^{V_{ID}/V_{th}}} - \frac{1}{1 + e^{-V_{ID}/V_{th}}} \right)$$

... which can be written as:

$$V_{OD} = -\alpha_F I_{BIAS} R_C \tanh(V_{ID}/2V_{th})$$

Operational Amplifiers

- Two-port (differential) small-signal model of an op amp



- Ideal “general purpose” op amp:

$R_{id} \rightarrow \text{infinity}$, $R_{out} \rightarrow 0$, $a_{vd} \rightarrow \text{infinity}$

Examples: 741 op amp has

$R_{id} = 2.7 \text{ M}\Omega$, $R_{out} = 47 \text{ }\Omega$, $a_{vd} = 300,000$ (approx).

MOS inputs $\rightarrow$ can get near-infinite differential input resistance

- *Many* other specifications ...

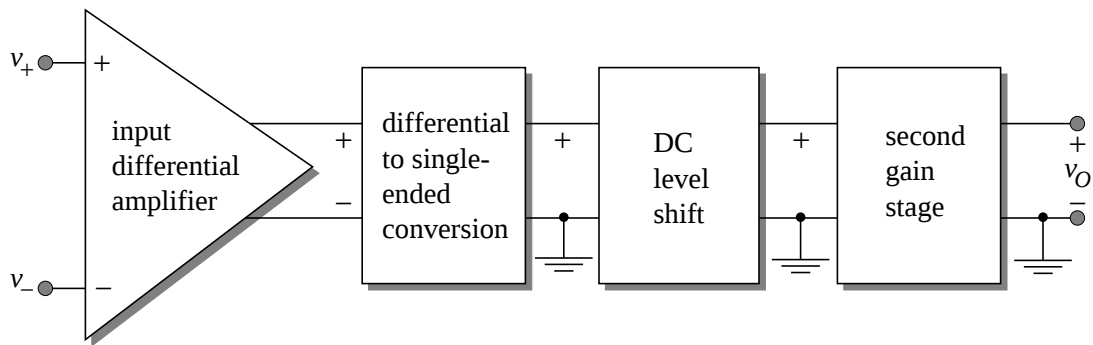
DC input common-mode voltage range and output swings

output current sourcing (out) or sinking (in) capability

offset voltage and its temperature dependence

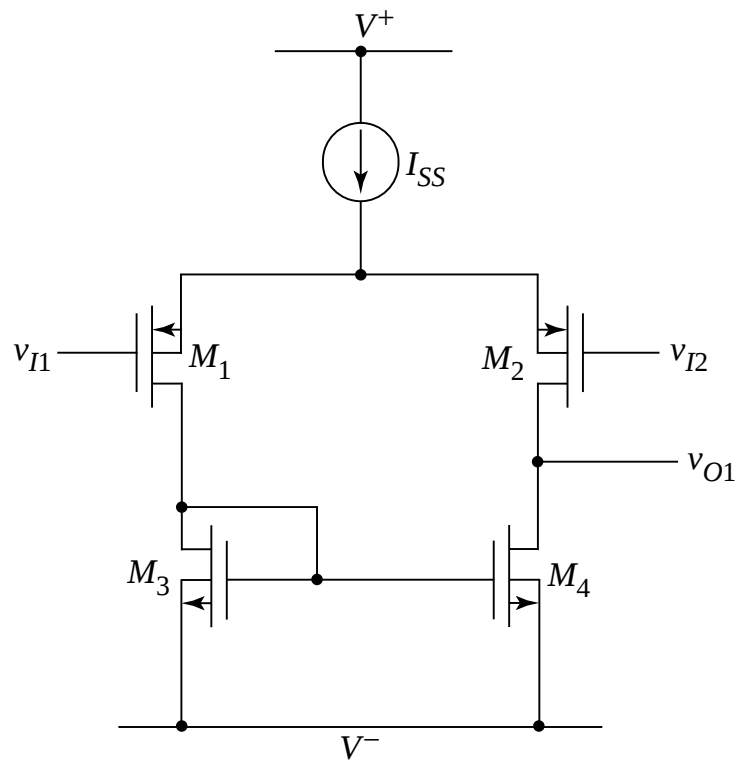
Internal Op Amps

- “Internal” op amp: loads are *capacitive* --> no need for R_{out} --> $0\ \Omega$
therefore, *no* output stage (common-collector or common-drain)
- Building block construction of an internal operational amplifier:



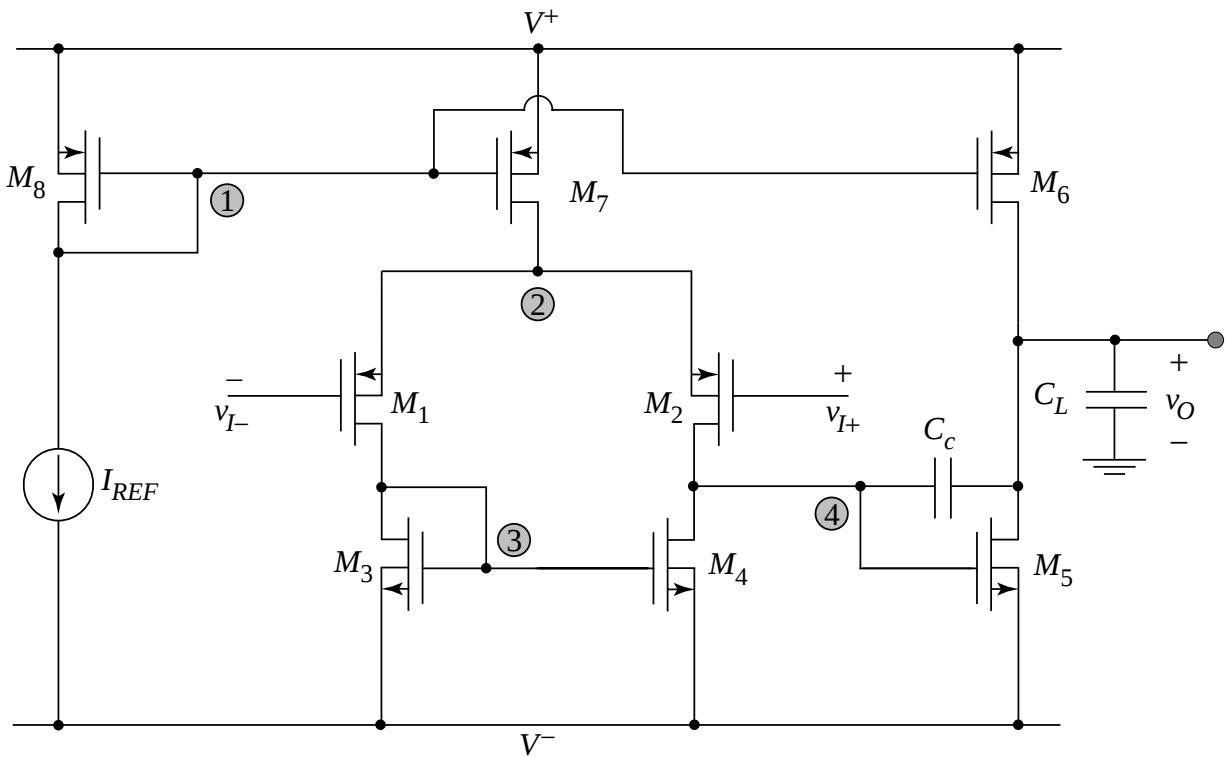
Differential Input Stage

- By using a current-mirror, we can implement differential-to-single ended conversion together with the differential input stage (without loss of 3 dB gain)
simple MOS version of input stage



Basic Two-Stage CMOS Op Amp Topology

- Add a second common-source gain stage to boost the overall voltage gain

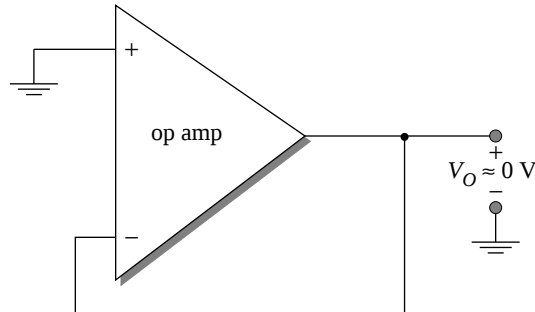


Capacitor C_c is important in the op amp frequency response

DC output is assumed to be $V_O = 0$ V

DC Bias Solution

- High gain --> place op amp in unity gain feedback loop to establish a stable DC operating point



■ Node 1

The source-gate voltage is defined by the DC current in M_8

$$V_1 = V^+ - \left(-V_{Tp} + \sqrt{\frac{2I_{REF}}{\mu_p C_{ox}(W/L)_8}} \right)$$

■ Node 2

The input voltages are at (nearly) zero volts, so the source-gate voltage of M_1 and M_2 determines V_2

$$V_2 = -V_{Tp} + \sqrt{\frac{2(-I_{D7}/2)}{\mu_p C_{ox}(W/L)_{1,2}}}$$

■ Node 3

The voltage is set by diode-connected M_3

$$V_3 = V^- + V_{Tn} + \sqrt{\frac{2(-I_{D7}/2)}{\mu_n C_{ox}(W/L)_{3,4}}}$$

DC Bias Solution (Cont.)

- Node 4

$$V_4 = V^- + V_{Tn} + \sqrt{\frac{2(-I_{D6})}{\mu_n C_{ox}(W/L)_5}}$$

- DC voltages of drains of M_1 and M_2 should be matched to avoid a systematic offset --> $V_3 = V_4$

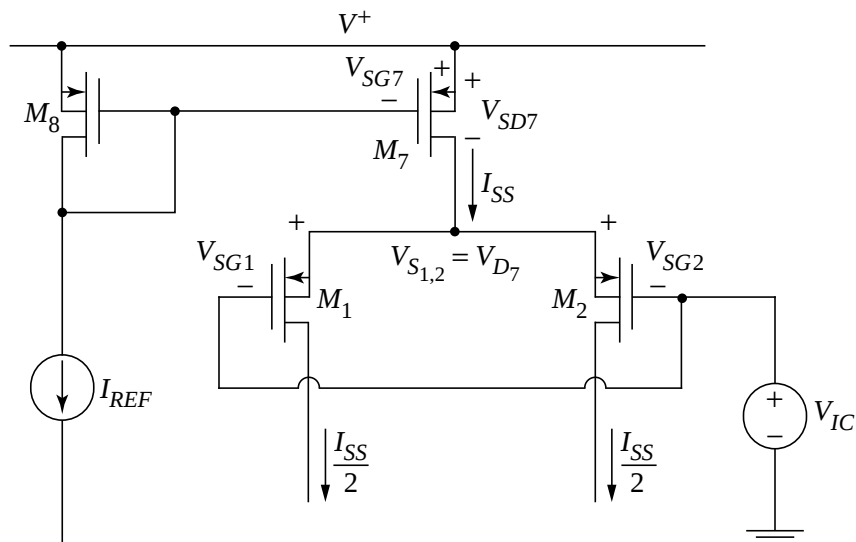
$$\sqrt{\frac{2(-I_{D7}/2)}{\mu_n C_{ox}(W/L)_{3,4}}} = \sqrt{\frac{2(-I_{D6})}{\mu_n C_{ox}(W/L)_5}}$$

$$\frac{-I_{D6}}{-I_{D7}} = \frac{(W/L)_5}{2(W/L)_{3,4}} = \frac{(W/L)_6}{(W/L)_7}$$

where the second equality follows from $V_{SG6} = V_{SG7}$

Common-Mode Input Voltage Range

- As V_{IC} increases, Node 2 follows and eventually M_7 will enter the triode region



$$V_{SD7} = V^+ - (V_{IC} + V_{SG1})$$

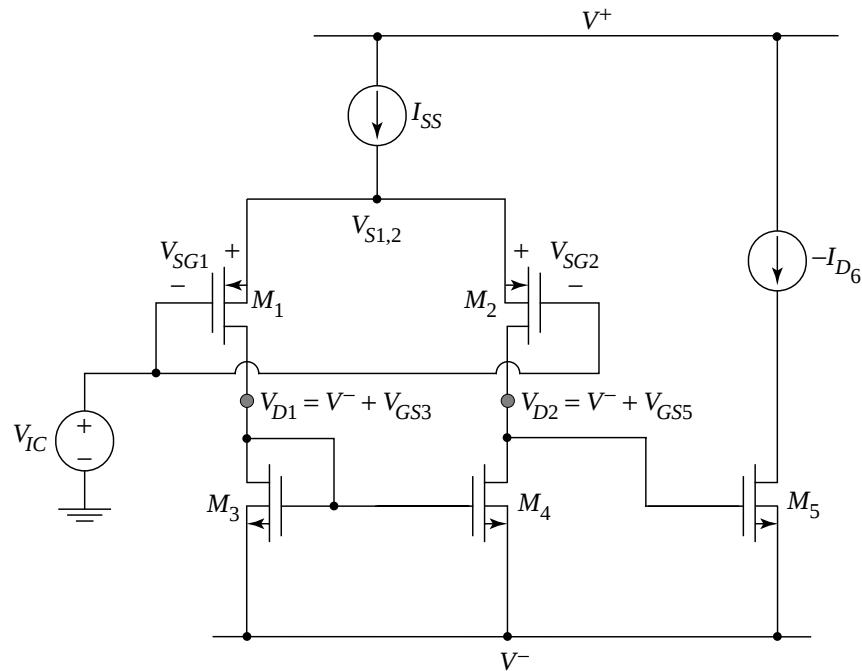
Maximum input common-mode voltage:

$$V_{SD7(sat)} = V_{SG7} + V_{Tp} = V^+ - (V_{IC,max} + V_{SG1})$$

$$V_{IC,max} = V^+ - V_{Tp} - V_{SG1} - V_{SG7}$$

Common-Mode Input Voltage Range (Cont.)

- As V_{IC} decreases, the input pair will eventually enter the triode region



$$V_{SD1} = (V_{IC} + V_{SG1}) - (V^- + V_{GS3}) \geq V_{SG1} + V_{Tp}$$

When M_1 just enters the triode region,

$$V_{IC,min} = V^- + V_{GS3} + V_{Tp} = V^- + V_{Tp} + V_{Tn} + \sqrt{\frac{2(I_{SS}/2)}{\mu_n C_{ox}(W/L)_3}}$$

Output Voltage Range

- The output node can increase until M_6 enters the triode region

$$V_{SD6} = V^+ - V_O \geq V_{SG6} + V_{Tp}$$

so the maximum output voltage is

$$V_{O,max} = V^+ - V_{Tp} - V_{SG6} = V^+ - \sqrt{\frac{2(-I_{D6})}{\mu_p C_{ox}(W/L)_6}}$$

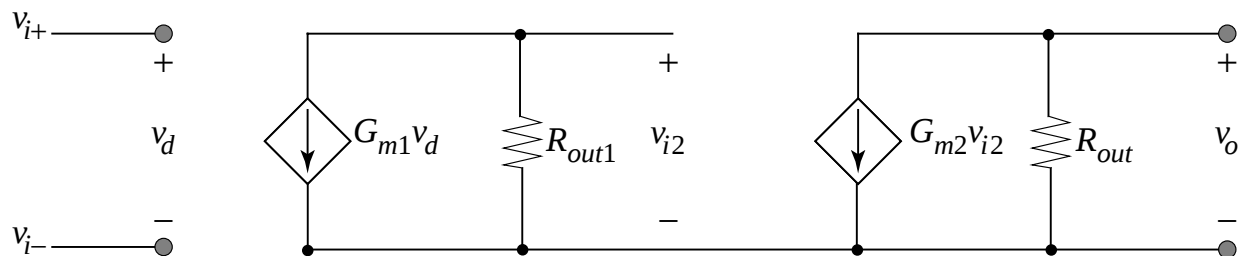
- Similarly, the output node can decrease until M_5 enters the triode region

$$V_{DS5} = V_O - V^- \geq V_{GS5} - V_{Tn}$$

$$V_{O,min} = V^- + \sqrt{\frac{2(-I_{D6})}{\mu_n C_{ox}(W/L)_5}}$$

Small-Signal Analysis of CMOS Two-Stage Op Amp

- Cascade two-port models of differential amplifier with current-mirror supply (input stage) and common-source amplifier with current supply (second gain stage)



- First stage:

polarity of G_{m1} is inverted to reflect reversal of input terminals ... which is done to make the overall gain positive for $v_d > 0$

$$G_{m1} = g_{m1}$$

$$R_{out1} = r_{o2} \parallel r_{o4}$$

- Second stage:

$$G_{m2} = g_{m5}$$

$$R_{out} = r_{o5} \parallel r_{o6}$$

$$a_{vdo} = (-G_{m1} R_{out1})(-G_{m2} R_{out})$$

$$a_{vdo} = g_{m1}(r_{o2} \parallel r_{o4})g_{m5}(r_{o5} \parallel r_{o6})$$

Two-Stage CMOS Design Example

■ Design constraints

Typical situation for an internal op amp: area and power are both limited.

Simplified area constraint -- set $W_{max} = 150 \mu\text{m}$

(for minimize channel-length modulation, set $L_{min} = 3 \mu\text{m}$)

Set DC power budget at 1.25 mW (including reference current) for case where we have symmetrical supplies: $V^+ = 2.5 \text{ V}$ and $V^- = -2.5 \text{ V}$.

■ Initial Transistor Sizing:

Make $(W/L)_1 = (150 \mu\text{m} / 3 \mu\text{m})$ in order to maximize G_{m1} and maximize common-mode input voltage range

DC currents: assume $I_{REF} = 50 \mu\text{A}$

Set DC bias current of differential amplifier = DC bias of common-source stage = $100 \mu\text{A}$ each as a first-cut --> total current drawn is $250 \mu\text{A}$ --> power spec. is just met

Transistor dimensions: $(W/L)_5 = (150 \mu\text{m} / 3 \mu\text{m})$ to maximize g_{m5}

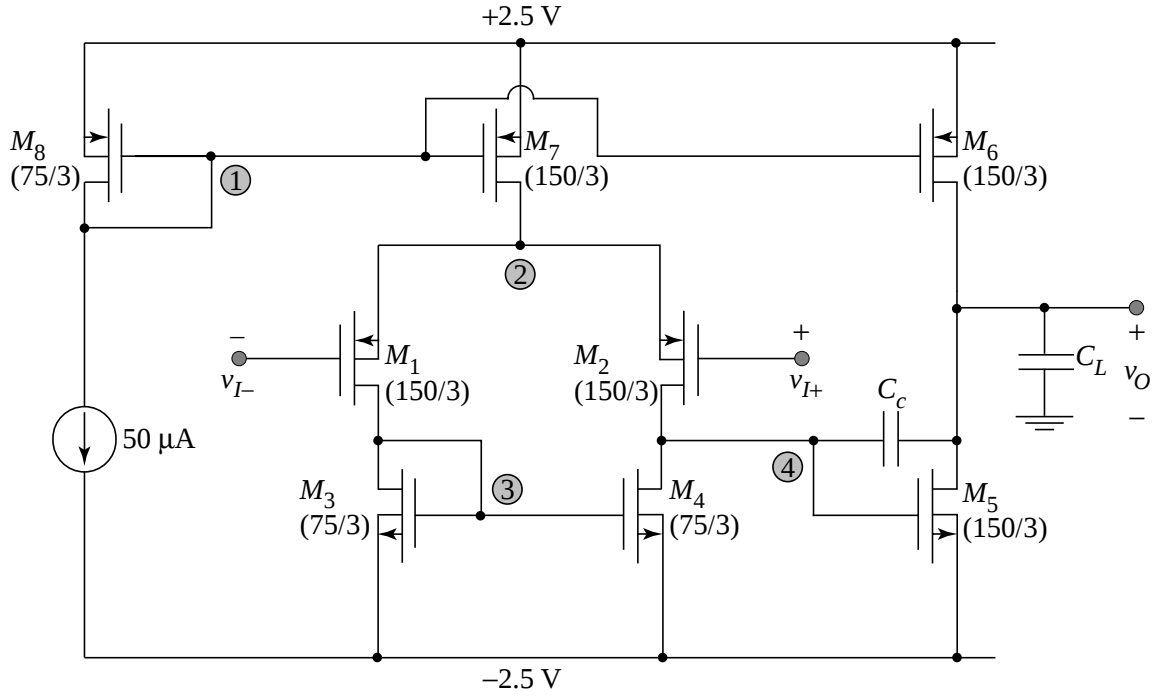
$$\frac{(W/L)_5}{2(W/L)_{3,4}} = \frac{-I_{D6}}{I_{D7}} = \frac{100 \mu\text{A}}{100 \mu\text{A}} = 1$$

Therefore $(W/L)_{3,4} = (W/L)_5 / 2 = 25 \rightarrow W_{3,4} = 75 \mu\text{m}$ since we use L_{min} to save area.

For symmetrical output swing, we set $(W/L)_6 = (W/L)_5 = (150 \mu\text{m} / 3 \mu\text{m})$

To maximize common-mode input range, we also set $(W/L)_7 = (150 \mu\text{m} / 3 \mu\text{m})$

First-Cut CMOS Two-Stage Op Amp



n-channel MOSFET

$\mu_n C_{ox} = 50 \frac{\mu A}{V^2}$	$t_{ox} = 15 \text{ nm}$	$C_{ov} = 0.5 \text{ fF}/\mu m$	$\phi_{Bn} = 0.95 \text{ V}$
$V_{TO n} = 1.0 \text{ V}$	$\lambda_n = \frac{0.1(\mu m/V)}{L}$	$C_{jno} = 0.1 \text{ fF}/\mu m^2$	$m_{jn} = 0.5$
$\gamma_n = 0.6 \text{ V}^{1/2}$	$2\phi_p = -0.8 \text{ V}$	$C_{jsw n} = 0.5 \text{ fF}/\mu m$	$m_{jsw n} = 0.33$

p-channel MOSFET

$\mu_p C_{ox} = 25 \frac{\mu A}{V^2}$	$t_{ox} = 15 \text{ nm}$	$C_{ov} = 0.5 \text{ fF}/\mu m$	$\phi_{Bp} = 0.95 \text{ V}$
$V_{TO p} = -1.0 \text{ V}$	$\lambda_p = \frac{0.1(\mu m/V)}{L}$	$C_{jpo} = 0.3 \text{ fF}/\mu m^2$	$m_{jp} = 0.5$
$\gamma_p = 0.6 \text{ V}^{1/2}$	$2\phi_n = 0.8 \text{ V}$	$C_{jsw p} = 0.35 \text{ fF}/\mu m$	$m_{jsw p} = 0.33$

DC Bias Solution

- Assume that the DC input voltages are $V_{I+} = V_{I-} = 0 \text{ V}$ and $V_O = 0 \text{ V}$

- Input common-mode voltage range

$$V_{IC,max} = 2.5 \text{ V} - (-1 \text{ V}) - 1.28 \text{ V} - 1.4 \text{ V} = 0.82 \text{ V}$$

$$V_{IC,min} = -2.5 \text{ V} + 1.28 \text{ V} + (-1 \text{ V}) = -2.22 \text{ V}$$

room for improvement in the upper limit -- possible at the expense of increased area (W/L) ratios must be increased.

- Output voltage swing

$$V_{O,max} = 2.5 \text{ V} - 0.4 \text{ V} = 2.1 \text{ V}$$

$$V_{O,min} = -2.5 \text{ V} + 0.28 \text{ V} = -2.22 \text{ V}$$

output range is nearly symmetrical and adequate

Small-Signal Performance

- Small-signal parameters:

$$g_{m1} = g_{m2} = 357 \mu\text{S}$$

$$g_{m5} = 2 g_{m1} = 714 \mu\text{S}$$

$$r_{o2} = r_{o4} = 600 \text{ k}\Omega$$

$$r_{o5} = r_{o6} = 300 \text{ k}\Omega$$

- Differential voltage gain:

$$a_{vdo} = (0.357)(600 || 600)(714)(300 || 300) = 1.15 \times 10^4$$

in decibels, $|a_{vdo}|_{\text{dB}} = 81 \text{ dB}$.